

ABSTRACT

5 An insulation layer is formed on the substrate of
a semiconductor wafer. A bottom electrode is formed
on the surface of the insulation layer followed by
forming a dielectric layer to cover the bottom electrode.
Thereafter, an etching process forms an upper electrode
10 hole within the dielectric layer to connect to the
surface of the bottom electrode. A spacer is formed
around the walls within the upper electrode hole. A
capacitor dielectric layer is then formed on the surface
of the dielectric layer, on the bottom within the upper
electrode hole, and on the spacer. Finally, an upper
15 electrode is formed within the upper electrode hole
to complete fabrication of a capacitor.